



ESI - HI2200 & HI2300 - HIGH TEMPERATURE PRESSURE SENSOR

HI2200-0001AB

10-20mV/V, 0..1 bar, G1/4, 1M cable

- Silicon-on-sapphire sensor technology
- Media temperature up to 200°C
- Ambient temperature up to 200°C
- Good chemical compatibility for a range of applications



Product description

The ESI Technology HI2200 & HI2300 high temperature pressure sensor series is designed to operate in applications with high demands on media and ambient temperature effects.

The unique Silicon-on-Sapphire (SOS) sensor technology provides outstanding insulating properties which means this pressure sensor can still give great performance and excellent stability over such a wide temperature range of 200°C. The sensor starts from 0 - 1 bar up to 0 - 1500 bar with a total of nine standard pressure ranges, two options of output (10-20 mV/V or 10 mV/V) and also two different electrical connections (1 meter PTFE insulated flying lead or MIL-C-26482 6 pin bayonet).

Application examples

- Furnaces
- Process
- Tanks
- Thermal chambers

Specifications

Ambient temperature	-40..200°C
Approvals	CE, IEC
Electrical connection	1m PTFE insulated flying lead
EMC	EN61000-6-4, EN61000-6-2
Linearity	≤±0.1% BSFL
Materials Wetted Parts	Titanium alloy
Media temperature	-50..200°C
Output	10-20mV/V

Overpressure protection	2 bar
Pressure Range Max	1
Pressure Range Min	0
Pressure reference	Gauge
Process connection	G1/4
Sensor technology	Silicon-on-Sapphire
Storage temperature	5..40°C
Supply voltage	10 V DC (5-15 V)

